

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of) Art Unit: 2812
Shunpei YAMAZAKI et al.) Examiner: S. Isaac
Serial No. 10/072,931)
Filed: February 12, 2002)
For: METHOD OF MANUFACTURING) Date: October 30, 2002
A SEMICONDUCTOR DEVICE)
)

#8/A
12-10-02
Payton

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

RECEIVED
OCT 30 2002
OFFICE OF PETITIONS

Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please add new claims 46-77 as follows:

21
-46. A method of manufacturing a semiconductor device comprising:
 forming a first semiconductor film having an amorphous structure over a
 substrate;
 providing the first semiconductor film with a material for promoting
 crystallization;
 heating the first semiconductor film for crystallizing;
 irradiating the first semiconductor film with a laser light for improving
 crystallinity;
 forming a barrier layer over the first semiconductor film having crystalline
 structure;
 forming a second semiconductor film over the barrier layer;
 forming a third semiconductor film over the second semiconductor film, the
 third semiconductor film comprising an inert gas element;